

PbS near-infrared detector Multi-Pixel thin-film encapsulated

Features

- Bondable electrode for COB mounting
- Very high sensitivity
- Suitable for automated wire-bonding
- Room temperature operation

Applications

- NIR spectroscopy
- Fire and spark detection
- Flame and moisture monitoring
- Gas detection

Electrical and optical characteristics per pixel

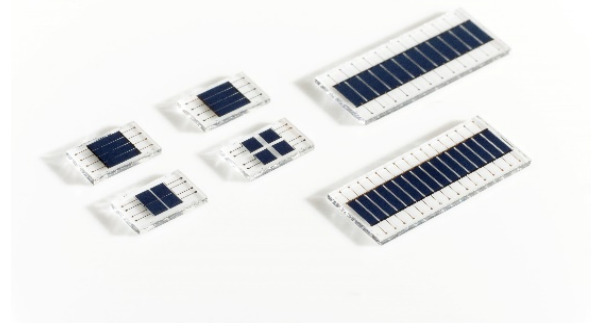
Element temperature [°C]	Peak wavelength λ_P [μm]	20% cut-off wavelength λ_C [μm]	Peak D* (620 Hz, 1 Hz) [cm·Hz ^{1/2} /W]		Time constant [μs]	Dark resistance R _D [MΩ]
	Typ.	Typ.	Typ.	Min.	Typ.	
22	2.7	2.9	1 · 10 ¹¹	0.5 · 10 ¹¹	200	0.3 - 15*

- Measured with 1550 nm LED, incident power 16 μW/cm²
- Measured in a voltage divider circuit with 50 V/mm
- Photo responsivity and detectivity are measured with constant load resistance (R_L = 1 MΩ) and calculated for matched resistance

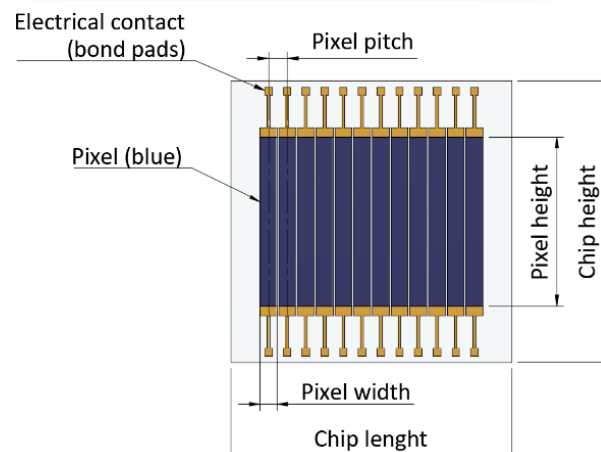
*depends on pixel geometry

Possible mechanical characteristics

- Number of lines 1 - 4
- Number of pixels 2 - 16
- Minimum pixel width 20 μm
- Minimum pixel height 20 μm
- Minimum pixel pitch 50 μm
- Minimal chip length 3000 μm
- Minimal chip height 3000 μm



Please contact us for an individual design:
info@hertzstueck.de



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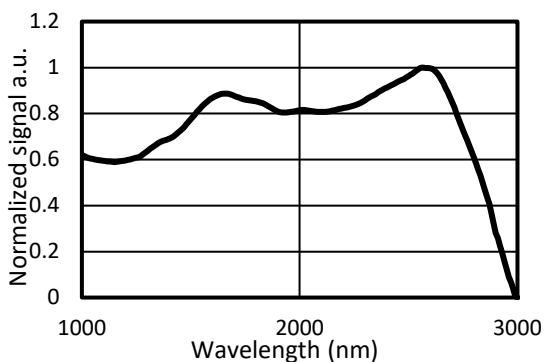


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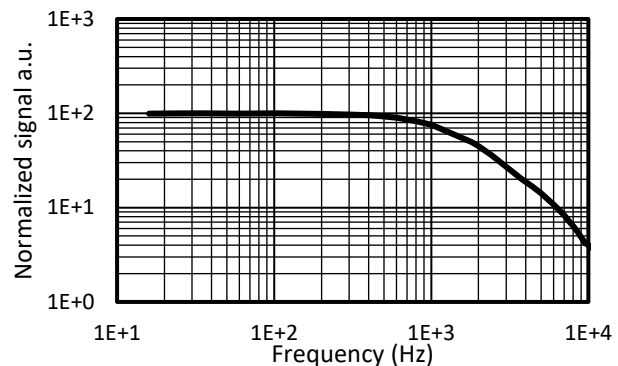
Exemplary mechanical characteristics

Type No.	Number of lines	Number of pixels	Pixel pitch [μm]	Pixel width [μm]	Pixel height [μm]	Operating temperature [°C]
PbS_MP_01x12_0200_0180x1800	1	12	200	180	x 1800	-30 to +70

Typical spectral response per pixel



Typical frequency response per pixel



Die attach

- Use clean, soft rubber tip for pick and place handling
- UV-curing is not suitable due to permanent damage by UV light exposure
- Element temperature should never exceed +70°C

Wire-bonding

- Electrodes are optimized for room temperature Al-wire-bonding
- Element temperature should never exceed +70°C

Options

- Individual housing
- Bonding onto PCB
- Integrated optics
- Evaluation-Kit available

Storage

- Storage temperature: -55°C to +70°C
- Exposure to UV light results in permanent damage
- Prevent exposure to UV and visible light

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trinamiX

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Handling

- Active area is scratch sensitive, protect top surface from any mechanical contact
- Ensure dust-free environment for device handling
- Operating temperature: -30°C to +70°C

Regulatory

For the use of Hertzstück™ PbS and PbSe infrared photodetectors in medical devices, monitoring and control instruments and consumer applications RoHS exemptions apply.

For automotive applications Hertzstück™ PbS and PbSe infrared photodetectors fall under ELV exemption.